

GN2A - GN2M

PRV : 50 - 1000 Volts
Io : 2.0 Amperes

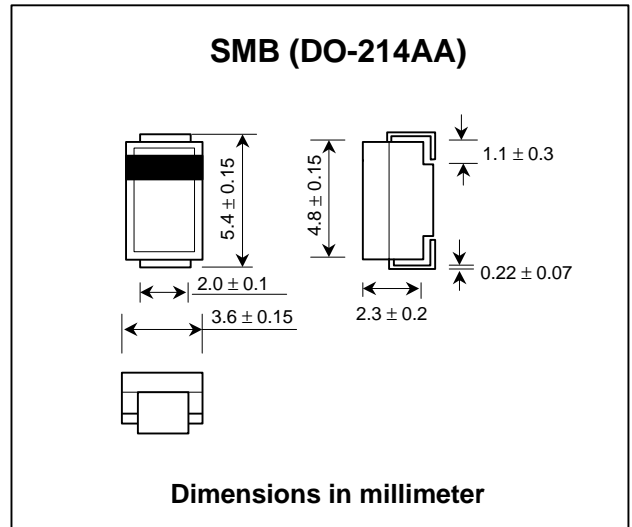
FEATURES :

- * Glass passivated chip
- * High current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SMB Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Lead Formed for Surface Mount
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.1079 gram

GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

RATING	SYMBOL	GN2A	GN2B	GN2D	GN2G	GN2J	GN2K	GN2M	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current $T_a = 50\text{ }^\circ\text{C}$	$I_{F(AV)}$	2.0							A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	50							A
Maximum Forward Voltage at $I_F = 2.0\text{ Amps.}$	V_F	1.0							V
Maximum DC Reverse Current $T_a = 25\text{ }^\circ\text{C}$ at rated DC Blocking Voltage $T_a = 100\text{ }^\circ\text{C}$	I_R	5.0							μA
	$I_{R(H)}$	50							μA
Typical Junction Capacitance (Note1)	C_J	75							pF
Junction Temperature Range	T_J	- 65 to + 150							$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 65 to + 150							$^\circ\text{C}$

Note :

(1) Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc

RATING AND CHARACTERISTIC CURVES (GN2A - GN2M)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

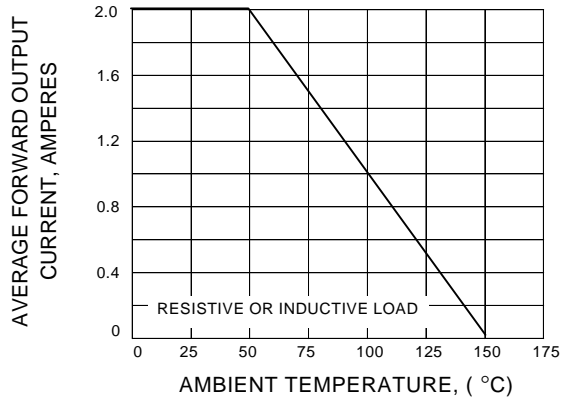


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

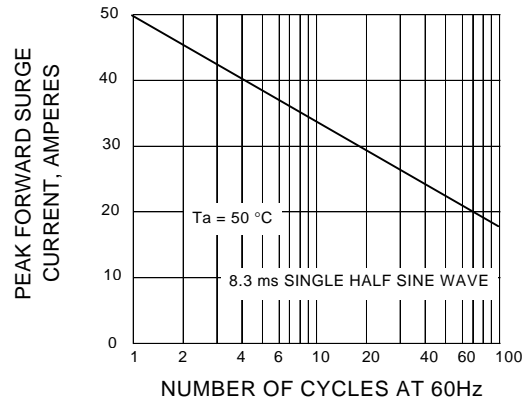


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

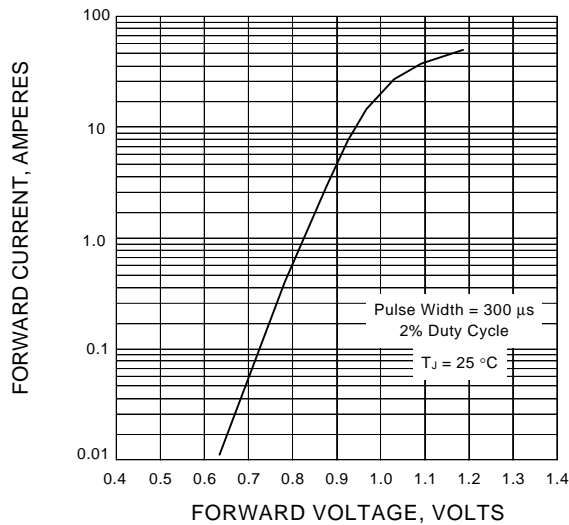


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

